

DATA-DRIVEN MISREGISTRATION PARAMETER CONFIGURATION AND MEASUREMENT SYSTEM AND METHOD

5 REFERENCE TO RELATED APPLICATIONS

Reference is hereby made to the following patents, which are related to the subject matter of the present application, the disclosures of which are hereby incorporated by reference:

- 10 Applicant's U.S. Patent No. 8,214,771, entitled SCATTEROMETRY METROLOGY TARGET DESIGN OPTIMIZATION, and issued on July 3, 2012; and
Applicant's U.S. Patent No. 9,910,953, entitled METROLOGY TARGET IDENTIFICATION, DESIGN AND VERIFICATION, and issued on March 6, 2018.

15 FIELD OF THE INVENTION

The present invention relates to measurement of misregistration in the manufacture of semiconductor devices generally.

20 BACKGROUND OF THE INVENTION

Various methods and systems are known for measurement of misregistration in the manufacture of semiconductor devices.

25 SUMMARY OF THE INVENTION

The present invention seeks to provide improved methods and systems for measurement of misregistration in the manufacture of semiconductor devices.

- 30 There is thus provided in accordance with a preferred embodiment of the present invention a data-driven misregistration parameter configuration and measurement method including simulating a plurality of measurement simulations of at least one multilayered semiconductor device, selected from a batch of multilayered semiconductor

devices intended to be identical, using a plurality of sets of measurement parameter configurations, thereby generating simulation data for the at least one multilayered semiconductor device, identifying at least one set of recommended measurement parameter configurations, which is selected from the plurality of sets of measurement parameter configurations, providing a multilayered semiconductor device selected from the batch of multilayered semiconductor devices, providing the at least one recommended set of measurement parameter configurations to a misregistration metrology tool having multiple possible sets of measurement parameter configurations, measuring at least one multilayered semiconductor device, selected from the batch of multilayered semiconductor devices intended to be identical, using the at least one recommended set of measurement parameter configurations, thereby generating measurement data for the at least one multilayered semiconductor device, thereafter identifying a final recommended set of measurement parameter configurations and measuring misregistration of at least one multilayered semiconductor device, selected from the batch of multilayered semiconductor devices intended to be identical, using the final recommended set of measurement parameter configurations.

In accordance with a preferred embodiment of the present invention, the final recommended set of measurement parameter configurations is identified based on best results of the measurement data for the at least one multilayered semiconductor device.

Preferably, the plurality of measurement simulations are metrology target design simulations. Preferably, the at least one recommended set of measurement parameter configurations is identified based on at least one of inaccuracy, Qmerit, focus sensitivity, throughput and contrast precision.

In accordance with a preferred embodiment of the present invention, the sets of measurement parameter configurations include at least one of an axis along which misregistration is measured, a region of interest of a metrology target, a numerical aperture used in misregistration measurement, a polarization of light used in misregistration measurement, wavelengths of light used in misregistration measurement, bandwidth of wavelengths of light used in misregistration measurement, an intensity of light used in misregistration measurement, a focal depth used in misregistration measurement and an apodizer used in misregistration measurement.

In accordance with a preferred embodiment of the present invention, the misregistration metrology tool is an imaging misregistration metrology tool. Alternatively, in accordance with a preferred embodiment of the present invention, the misregistration metrology tool is a scatterometry misregistration metrology tool.

5 In accordance with a preferred embodiment of the present invention the data-driven misregistration parameter configuration and measurement method also includes generating simulation signal data and comparing the simulation signal data to the measurement data for the at least one multilayered semiconductor device.

10 Preferably, the simulation signal data includes at least one of contrast, sensitivity and pupil image. Preferably, the data-driven misregistration parameter configuration and measurement method also includes indicating for which of the sets of measurement parameter configurations and for which portions of the multilayered semiconductor device a mismatch between the simulation signal data and the measurement data occurs and indicating possible root causes of the mismatch.

15 There is also provided in accordance with another preferred embodiment of the present invention a data-driven misregistration parameter configuration and measurement system including a semiconductor device measurement simulator, operative to simulate a plurality of measurement simulations of at least one multilayered semiconductor device, selected from a batch of multilayered semiconductor devices
20 intended to be identical, using a plurality of sets of measurement parameter configurations, thereby generating simulation data for the at least one multilayered semiconductor device, a simulation data analyzer, operative to identify at least one recommended set of measurement parameter configurations, which is selected from the plurality of sets of measurement parameter configurations and a misregistration
25 metrology tool having multiple possible sets of measurement parameter configurations, operative to receive the at least one recommended set of measurement parameter configurations and to measure misregistration of at least one multilayered semiconductor device, selected from the batch of multilayered semiconductor devices intended to be identical, using the at least one recommended set of measurement parameter
30 configurations, thereby generating measurement data for the at least one multilayered semiconductor device.

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention will be understood and appreciated more fully from the following detailed description, taken in conjunction with the drawings in which:

5 Fig. 1 is a simplified schematic illustration of a data-driven misregistration parameter configuration and measurement system; and

 Fig. 2 is a simplified flow chart illustrating a data-driven misregistration parameter configuration and measurement method useful by the data-driven misregistration parameter configuration and measurement system of Fig. 1.

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DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

Reference is now made to Fig. 1, which is a simplified schematic illustration of a data-driven misregistration parameter configuration and measurement system (DDMPCMS) 100. As seen in Fig. 1, DDMPCMS 100 includes a semiconductor device measurement simulator (SDMS) 110. SDMS 110 is operative to simulate a plurality of measurements of a multilayered semiconductor device, selected from a batch of multilayered semiconductor devices intended to be identical, using a plurality of measurement parameter configurations, thereby generating simulation data for the multilayered semiconductor device.

20 In a preferred embodiment of the present invention, SDMS 110 is embodied as a metrology target design (MTD) simulator, such as the one described in U.S. Patent No. 8,214,771 or in U.S. Patent No. 9,910,953, the disclosures of which are hereby incorporated by reference.

25 Preferably, SDMS 110 simulates a plurality of MTD simulations of at least one multilayered semiconductor device, selected from a batch of multilayered semiconductor devices intended to be identical, generating simulation data for the multilayered semiconductor device. Preferably, the MTD simulations include simulations of misregistration measurements designed to be measured by either imaging or scatterometry misregistration tools. Preferably, SDMS 110 simulates each misregistration measurement for the at least one multilayered semiconductor device using a different set of measurement parameter configurations.

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Parameters used in the MTD simulations including misregistration measurements designed to be measured by imaging misregistration tools may include, inter alia, an axis along which misregistration is measured, a region of interest of a metrology target, a numerical aperture used in misregistration measurement, a polarization of light used in misregistration measurement, wavelengths of light used in misregistration measurement, bandwidth of wavelengths of light used in misregistration measurement, an intensity of light used in misregistration measurement and a focal depth used in misregistration measurement. Parameters used in the MTD simulations including misregistration measurements designed to be measured by scatterometry misregistration tools may include, inter alia, an axis along which misregistration is measured, a region of interest of a metrology target, an apodizer used in misregistration measurement, a polarization of light used in misregistration measurement, wavelengths of light used in misregistration measurement, bandwidth of wavelengths of light used in misregistration measurement, an intensity of light used in misregistration measurement and a focal depth used in misregistration measurement.

In an alternative embodiment of the present invention, SDMS 110 simulates a plurality of simulation-to-measurement (S2M) simulations of at least one multilayered semiconductor device, selected from a batch of multilayered semiconductor devices intended to be identical, generating simulation data for the multilayered semiconductor device. Preferably, the S2M simulations' input includes characteristics of the multilayered semiconductor device. The characteristics may include, inter alia, index of refraction and dielectric constant. Preferably, SDMS 110 simulates each measurement for the at least one multilayered semiconductor device using a different set of measurement parameter configurations, and generates expected simulation signal data from each measurement. Expected simulation signal data may include, inter alia, contrast, sensitivity and pupil image.

DDMPCMS 100 preferably further includes a semiconductor device measurement simulation data analyzer (SDMSDA) 120, which analyzes simulation data for the at least one multilayered semiconductor device generated by SDMS 110 and identifies at least one recommended measurement parameter configuration, which is selected from the plurality of measurement parameter configurations used in the simulations run by SDMS 110.

In a preferred embodiment of the present invention, SDMSDA 120 evaluates quality metrics of the simulation data generated by SDMS 110. Quality metrics may include, inter alia, inaccuracy, Qmerit, focus sensitivity, throughput and contrast precision. The quality metrics of each simulation are compared to each other, and the measurement parameter configurations of the simulations having the most desirable quality metrics are identified as recommended measurement parameter configurations.

DDMPCMS 100 preferably further includes a misregistration metrology tool 130 having multiple possible measurement parameter configurations. Misregistration metrology tool 130 uses the at least one recommended measurement parameter configuration identified by SDMSDA 120 to measure a multilayered semiconductor device intended to be identical to the multilayered semiconductor device simulated by SDMS 110. In a preferred embodiment of the present invention, misregistration metrology tool 130 measures the multilayered semiconductor device with each of the plurality of recommended measurement parameter configurations, and a final measurement parameter configuration is chosen based on best results of measurements performed by misregistration metrology tool 130.

Misregistration metrology tool 130 is preferably embodied either as an imaging misregistration metrology tool or as a scatterometry misregistration metrology tool. A typical imaging misregistration metrology tool, useful as misregistration metrology tool 130, is an Archer™ 600, commercially available from KLA Corporation of Milpitas, CA, USA. A typical scatterometry misregistration metrology tool, useful as misregistration metrology tool 130, is an ATL™ 100, commercially available from KLA Corporation of Milpitas, CA, USA.

In a case wherein SDMS 110 simulates S2M measurements, SDMSDA 120 compares the expected simulation signal data generated by SDMS 110 to the actual signal data generated by misregistration metrology tool 130. Signal data may include, inter alia, contrast, sensitivity and pupil image. If the difference between the expected and actual signal data exceeds a predetermined threshold, SDMSDA 120 preferably indicates for which sets of measurement parameter configurations used by misregistration metrology tool 130 and for which portions of the multilayered semiconductor device a mismatch between the simulation signal data and the measurement data occurs, and further indicates possible root causes of the mismatch.

Reference is now made to Fig. 2, which is a simplified flow chart illustrating a data-driven misregistration parameter configuration and measurement method 200 useful by DDMPCMS 100.

As seen at a first step 202, SDMS 110 simulates a plurality of
5 measurements of a multilayered semiconductor device, selected from a batch of multilayered semiconductor devices intended to be identical, using a plurality of measurement parameter configurations, thereby generating simulation data for the multilayered semiconductor device.

In a preferred use case, SDMS 110 simulates a plurality of MTD
10 simulations of at least one multilayered semiconductor device, selected from a batch of multilayered semiconductor devices intended to be identical, generating simulation data for each of the at least one multilayered semiconductor device. Preferably, the MTD simulations include misregistration measurements designed to be measured by either imaging or scatterometry misregistration tools. Preferably, SDMS 110 simulates each
15 misregistration measurement for each of the at least one multilayered semiconductor device using a different set of measurement parameter configurations.

Parameters used in the MTD simulations including misregistration measurements designed to be measured by imaging misregistration tools may include, inter alia, an axis along which misregistration is measured, a region of interest of a
20 metrology target, a numerical aperture used in misregistration measurement, a polarization of light used in misregistration measurement, wavelengths of light used in misregistration measurement, bandwidth of wavelengths of light used in misregistration measurement, an intensity of light used in misregistration measurement and a focal depth used in misregistration measurement. Parameters used in the MTD simulations including
25 misregistration measurements designed to be measured by scatterometry misregistration tools may include, inter alia, an axis along which misregistration is measured, a region of interest of a metrology target, an apodizer used in misregistration measurement, a polarization of light used in misregistration measurement, wavelengths of light used in misregistration measurement, bandwidth of wavelengths of light used in misregistration
30 measurement, an intensity of light used in misregistration measurement and a focal depth used in misregistration measurement.

Following step 202, at a next step 204, SDMSDA 120 analyzes simulation data generated at step 202. Then, at a next step 206, SDMSDA 120 identifies at least one recommended measurement parameter configuration, which is selected from the plurality of measurement parameter configurations used at step 202.

5 At step 204, SDMSDA 120 evaluates quality metrics of the simulation data generated at step 202. Quality metrics may include, inter alia, inaccuracy, Qmerit, focus sensitivity, throughput and contrast precision. The quality metrics of each simulation are compared to each other, and at step 206, at least one set of measurement parameter configurations of the simulations having the most desirable quality metrics is identified
10 as at least one recommended set of measurement parameter configurations.

 At a next step 208, misregistration metrology tool 130 uses at least one set of recommended measurement parameter configurations, selected from the at least one recommended set of measurement parameter configurations identified at step 206, to measure a multilayered semiconductor device intended to be identical to the multilayered
15 semiconductor device simulated at step 202. Then, at a next step 210, a decision is made whether or not to measure a multilayered semiconductor device, intended to be identical to the multilayered semiconductor device simulated at step 202, using an additional set of recommended measurement parameter configurations, selected from the at least one recommended set of measurement parameter configurations identified at step 206.

20 As seen at a next step 212, if a multilayered semiconductor device intended to be identical to the multilayered semiconductor device simulated at step 202 is to be measured using an additional set of recommended measurement parameter configurations, selected from the at least one recommended set of parameter configurations identified at step 206, misregistration metrology tool 130 uses an
25 additional set of recommended measurement parameter configurations, selected from the at least one recommended set of measurement parameter configurations identified at step 206, to measure a multilayered semiconductor device intended to be identical to the multilayered semiconductor device simulated at step 202.

 Following step 212, the method 200 returns to step 210 and a decision is
30 made whether or not to measure a multilayered semiconductor device intended to be identical to the multilayered semiconductor device simulated at step 202 using an

additional set of recommended measurement parameter configurations, selected from the at least one recommended set of parameter configurations identified at step 206.

As seen at a next step 214, if a multilayered semiconductor device intended to be identical to the multilayered semiconductor device simulated at step 202 is not to be measured using an additional set of recommended measurement parameter configurations, selected from the at least one recommended set of measurement parameter configurations identified at step 206, a final recommended set of measurement parameter configurations is identified. In a preferred embodiment of the present invention, the final set of recommended measurement parameter configurations is identified based on best results of measurements performed in steps 208 and 212.

In a case wherein SDMS 110 simulates S2M measurements, during step 214, SDMSDA 120 compares the expected simulation signal data generated at step 202 to the actual signal data generated at steps 208 and 212. Signal data may include, inter alia, contrast, sensitivity and pupil image. If the difference between the expected and actual signal data exceeds a predetermined threshold, at step 214 SDMSDA 120 indicates for which sets of measurement parameter configurations used by misregistration metrology tool 130 and for which portions of the multilayered semiconductor device a mismatch between the simulation signal data and the measurement data occurs, and further indicates possible root causes of the mismatch.

As seen at a next step 216, misregistration metrology tool 130 uses the final recommended set of measurement parameter configurations identified at step 214 to measure at least one additional multilayered semiconductor device, intended to be identical to the multilayered semiconductor device simulated at step 202.

It will be appreciated by persons skilled in the art that the present invention is not limited to what has been particularly shown and described hereinabove. The scope of the present invention includes both combinations and subcombinations of various features described hereinabove as well as modifications thereof, all of which are not in the prior art.